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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: Tamotsu OWADA et al. Group Art Unit: 2811

Serial No.: 10/694,826 Examiner: Nitin Parek

Filed: October 29, 2003 Confirmation No.: 9457

For: SILICON OXYCARBIDE, GROWTH METHOD OF SILICON OXYCARBIDE LAYER, SEMICONDUCTOR DEVICE AND MANUFACTURE METHOD FOR SEMICONDUCTOR DEVICE

Attorney Docket Number: 032060

Customer Number: 38834

## RESPONSE TO RESTRICTION REQUIREMENT

Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

December 13, 2004

Sir:

This paper is submitted in response to the Official Action dated December 1, 2004.

In the Action, restriction is required between Group I, (Claims 12-22); Group II, (Claims 6-11 and 23-30); and Group III (Claims 1-5).

Applicants hereby elect the subject matter of Group I, Claims (12-22) for prosecution in this application. This election is made without traverse, and it is understood that Applicants' rights to the filing of a divisional application directed to the non-elected subject matter under 35 U.S.C. §120 and 35 U.S.C. §121 are retained.

Response to Restriction Requirement Serial No. 10/694,826 Attorney Docket No. 032060

If this paper is not timely filed, Applicant(s) respectfully petition(s) for an appropriate extension of time. The fees for such an extension or any other fees that may be due with respect to this paper may be charged to Deposit Account No. 50-2866.

Respectfully submitted,

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